



60V N-CHANNEL SELF-PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

Product Summary

Continuous Drain Source Voltage: 60V

On-State Resistance: $200m\Omega$

Nominal Load Current (V_{IN} = 5V): 2.0A

Clamping Energy: 120mJ

Description

The ZXMS6005N8 is a self-protected low side IntelliFETTM MOSFET with logic level input. It integrates over-temperature, overcurrent, overvoltage (active clamp) and ESD protected logic level functionality. The ZXMS6005N8 is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Especially Suited for Loads with a High In-Rush Current such as Lamps and Motors
- All Types of Resistive, Inductive and Capacitive Loads in Switching Applications
- μC Compatible Power Switch for 12V and 24V DC Applications
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode Capability- the current-limiting protection circuitry is designed to deactivate at low VDS to minimize on-state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self-protect at low V_{DS}.

Features and Benefits

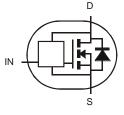
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection Input Protection (ESD)
- High Continuous Current Rating
- Totally Lead-Free & Fully RoHS Compliant (Notes 1& 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMS6005N8Q)

Mechanical Data

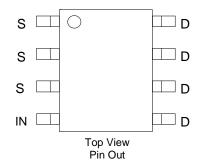
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 80.2mg (Approximate)



Top View



Device Symbol



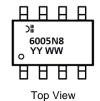
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMS6005N8-13	6005N8	13	12	2,500 Units

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃\\\ = Manufacturer's Marking 6005N8 = Product Type Marking Code YYWW = Date Code Marking YY: Year WW: Week: 01~52; 52 represents 52 and 53 week

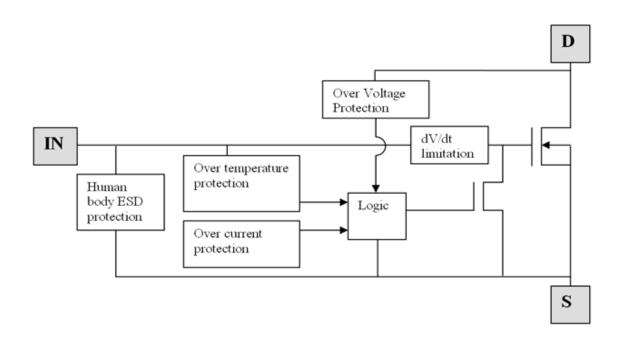
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ZXMS6005N8 Document number: DS38473 Rev. 3 - 2 1 of 8

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Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	24	V
Continuous Input Voltage	V _{IN}	-0.5 to +6	V
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} $<$ -0.2V or V _{IN} $>$ 6V	I _{IN}	No Limit I _{IN} ≤ 2	mA
Pulsed Drain Current @V _{IN} = 3.3V	I _{DM}	5	А
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	6	A
Continuous Source Current (Body Diode) (Note 5)	I _S	2.5	A
Pulsed Source Current (Body Diode)	I _{SM}	10	Α
Unclamped Single Pulse Inductive Energy, T _J = +25°C, I _D = 0.5A, V _{DD} = 24V	E _{AS}	120	mJ
Electrostatic Discharge (Human Body Model)	V _{HBM}	4,000	V
Charged Device Model	V _{CDM}	1,000	V

Recommended Operating Conditions

The ZXMS6005N8 is optimized to use with μC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V _{IN}	0	5.5	V
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to be On	VIH	3	5.5	V
Low Level Input Voltage for MOSFET to be Off	V _{IL}	0	0.7	V
Peripheral Supply Voltage (Voltage to which Load is Referred)	V _P	0	24	V

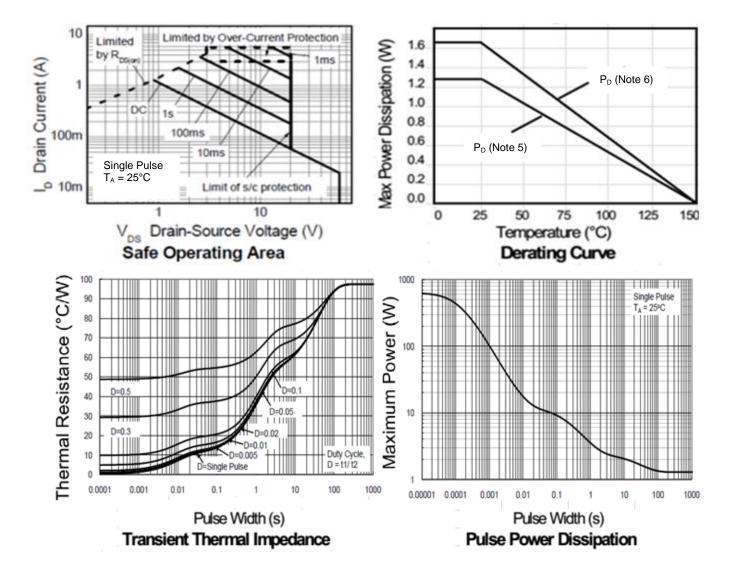


Thermal Resistance (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation @T _A = +25°C (Note 5) Linear Derating Factor	P _D	1.28 10	W mW/°C
Power Dissipation @T _A = +25°C (Note 6) Linear Derating Factor	P _D	1.65 12.4	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	98	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	76	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	12	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 7. Thermal resistance between junction and the mounting surfaces of drain and source pins.





Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	65	70	V	I _D = 10mA
0"0' 1 0 1 0		_	_	1	μА	V _{DS} = 12V, V _{IN} = 0V
Off-State Drain Current	I _{DSS}	_	_	2		$V_{DS} = 36V, \ V_{IN} = 0V$
Input Threshold Voltage	V _{IN(TH)}	0.7	1	1.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$
Input Current	1	1	60	100	μΑ	$V_{IN} = 3V$
input Current	I _{IN}	1	120	200		$V_{IN} = 5V$
Input Current while Overtemperature Active		1	_	300	μΑ	$V_{IN} = 5V$
Static Drain-Source On-State Resistance	Page	1	170	250	mΩ	$V_{IN} = 3V, I_D = 1.0A$
Static Diani-Source On-State Resistance	R _{DS(ON)}	1	150	200	11122	$V_{IN} = 5V, I_D = 1.0A$
Continuous Drain Current (Note 5)		1.4	_	_	- A	$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Diain Current (Note 3)	I _D	1.6	_	_		$V_{IN} = 5V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.9	_	_		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Diain Current (Note 0)		2.0	_	_		$V_{IN} = 5V, T_A = +25^{\circ}C$
Current Limit (Note 8)	I _{D(LIM)}	2.2	5	_	A	$V_{IN} = 3V$
Current Limit (Note 6)		3.3	7	_		$V_{IN} = 5V$
Dynamic Characteristics						
Turn-On Delay Time	t _{D(ON)}	1	5	_		$V_{DD} = 12V$, $I_D = 0.5A$, $V_{GS} = 5V$
Rise Time	t_R	-	14	_		
Turn-Off Delay Time	t _{D(OFF)}	_	34	_	μs	
Fall Time	t_F	_	19	_		
Overtemperature Protection						
Thermal Overload Trip Temperature (Note 9)	T_{JT}	+150	+175	_	°C	_
Thermal Hysteresis (Note 9)	ΔT_{JT}	_	+10	_	°C	_

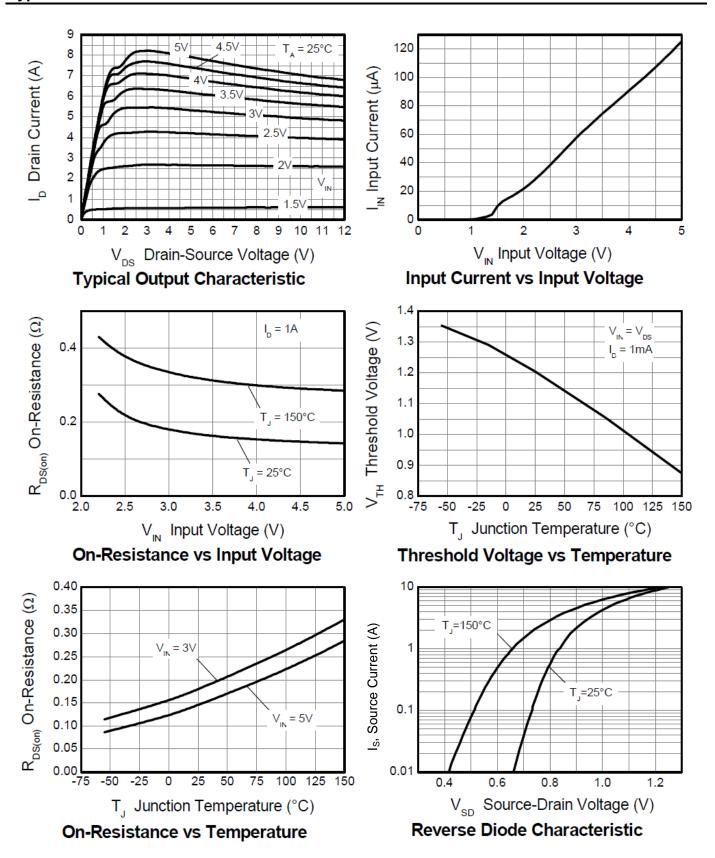
Notes:

^{8.} The drain current is restricted only when the device is in saturation (see Typical Output Characteristic graph). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

Overtemperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand overtemperature for extended periods.

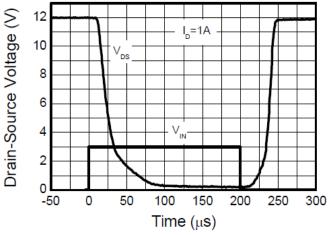


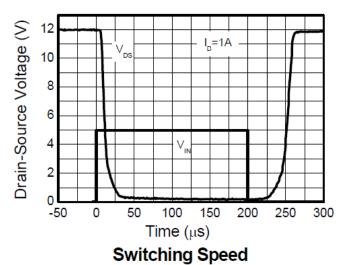
Typical Characteristics



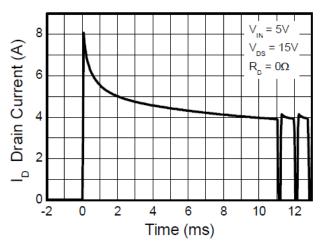


Typical Characteristics (Cont.)





Switching Speed



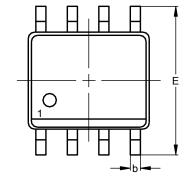
Typical Short Circuit Protection

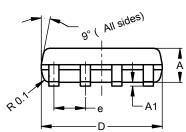


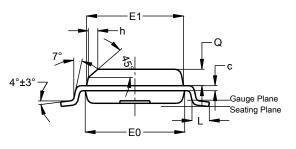
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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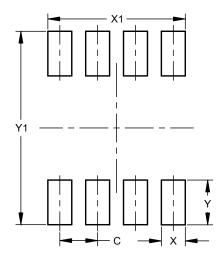


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Dim	Min	Max	Тур	
Α	1.40	1.50	1.45	
A1	0.10	0.20	0.15	
b	0.30	0.50	0.40	
C	0.15	0.25	0.20	
D	4.85	4.95	4.90	
Е	5.90	6.10	6.00	
E1	3.80	3.90	3.85	
E0	3.85	3.95	3.90	
е			1.27	
h	-		0.35	
١	0.62	0.82	0.72	
ø	0.60	0.70	0.65	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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Dimensions	Value (in mm)	
С	1.27	
Х	0.802	
X1	4.612	
Y	1.505	
Y1	6.50	



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